

SuperMOS – SOT-23 -20V BV_{DSS} , 30m Ω $R_{DS(on)}$, P-channel MOSFET

1. Description

The AO3415 is P-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product AO3415 is Pb-free.

2. Features

- -20V, $R_{DS(ON)}$ =30m Ω (Typ.) @ V_{GS} =-4.5V
- $R_{DS(ON)}$ =36m Ω (Typ.) @ V_{GS} =-2.5V
- Fast Switching
- High density cell design for low $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

3. Applications

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Size
AO3415	SOT-23	R15	Halogen free	Tape & Reel	3,000 PCS	UL 94V-0	7 inches

Table-1 Ordering information

5. Pin Configuration and Functions

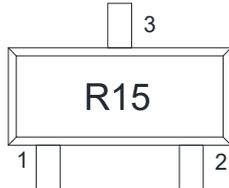
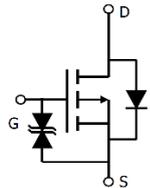
Pin	Function	Outline	Circuit Diagram
1	Gate		
2	Source		
3	Drain		

Table-2 Pin configuration

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	BV_{DSS}	-20	V
Gate-Source Voltage	V_{GS}	± 10	V
Continuous Drain Current	I_D	$T_A=25^\circ\text{C}$	-4.9
		$T_A=75^\circ\text{C}$	-3.8
Maximum Power Dissipation	P_D	$T_A=25^\circ\text{C}$	1.39
		$T_A=75^\circ\text{C}$	0.83
Pulsed Drain Current	I_{DM}	-15.6	A
Operating Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$

Thermal resistance ratings

Single Operation				
Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance ($t \leq 10\text{s}$)	$R_{\theta JA}$	65	90	$^\circ\text{C/W}$
Junction-to-Lead Thermal Resistance	$R_{\theta JL}$	43	52	

Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS}=0V, V_{DS}=-20V$			-1	μA
Gate-to-source Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$			± 10	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-0.5	-0.7	-0.9	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-4A$		30	37	$m\Omega$
		$V_{GS}=-2.5V, I_D=-4A$		36	47	
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-4A$			40	S
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{ISS}	$V_{GS}=0V, V_{DS}=-10V$ $f=1MHz$		750		pF
Output Capacitance	C_{OSS}			115		
Reverse Transfer Capacitance	C_{RSS}			80		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS}=-4.5V, V_{DS}=-10V$ $I_D=-4A$		9.5		nC
Gate-to-Source Charge	Q_{GS}			1		
Gate-to-Drain Charge	Q_{GD}			2.3		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS}=-4.5V, V_{DS}=-10V$ $R_L=2.5\Omega, R_G=3\Omega$		13		ns
Rise Time	t_r			10		
Turn-Off Delay Time	$t_{d(OFF)}$			20		
Fall Time	t_f			30		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	$V_{GS}=0V, I_{SD}=-1.0A$			-1.5	V

7. Typical Characteristic

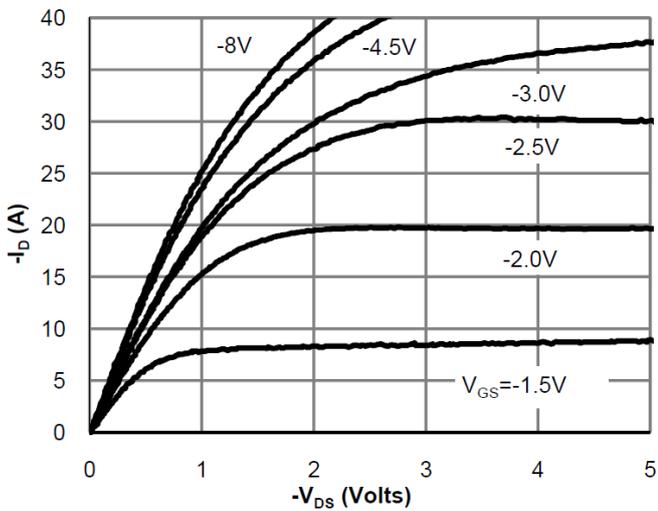


Fig 1: On-Region Characteristics

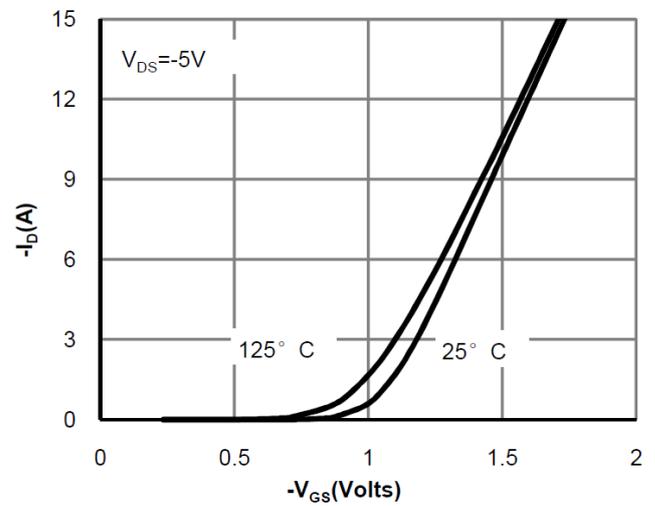


Figure 2: Transfer Characteristics

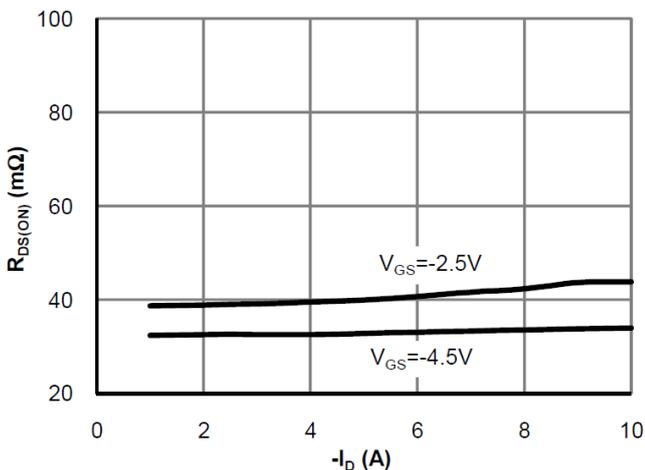


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

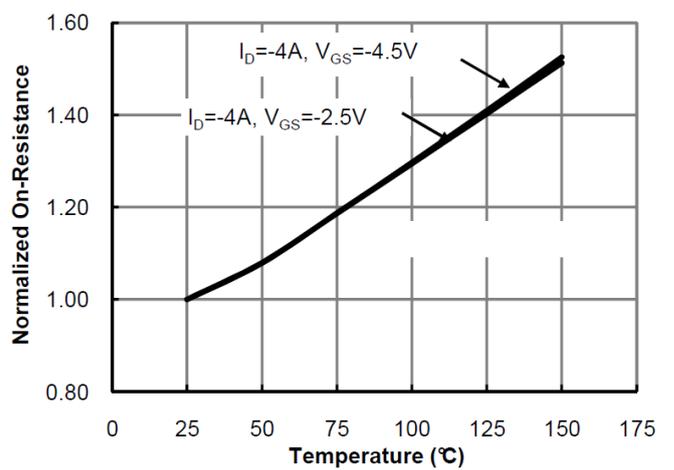


Figure 4: On-Resistance vs. Junction Temperature

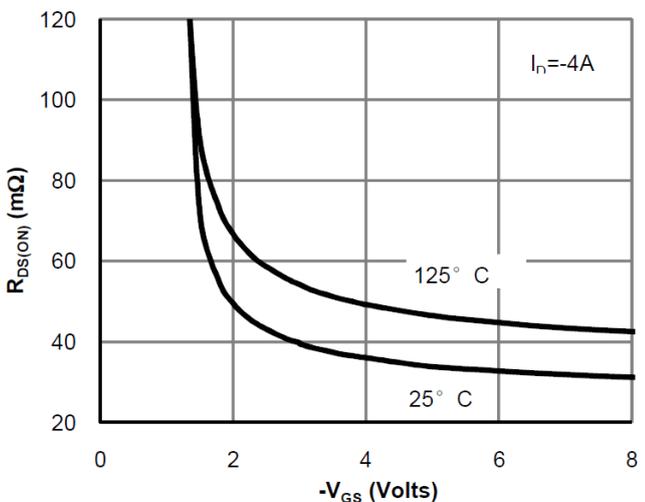


Figure 5: On-Resistance vs. Gate-Source Voltage

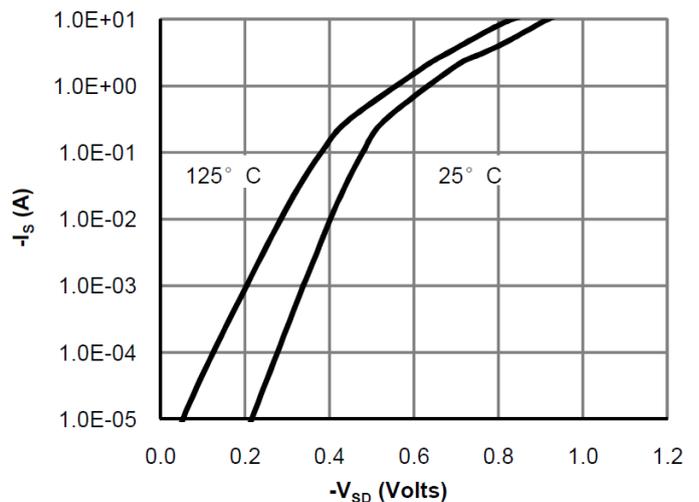


Figure 6: Body-Diode Characteristics

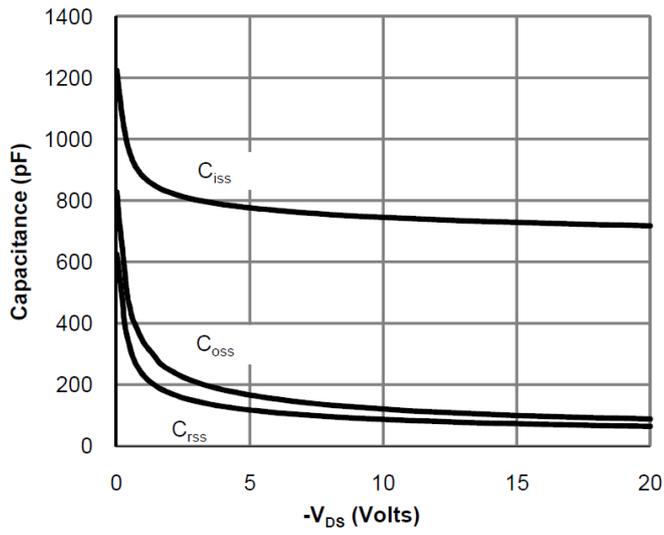
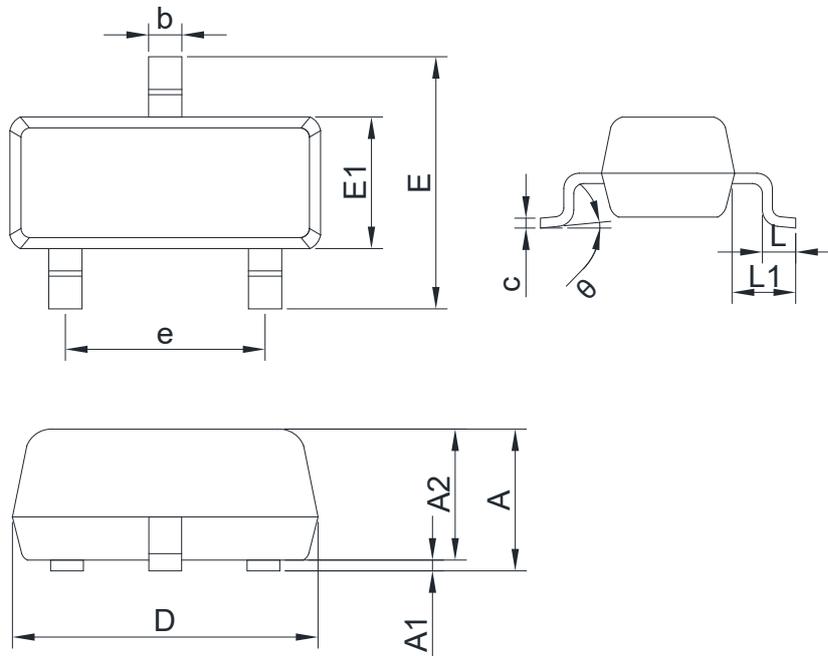


Figure 7: Capacitance Characteristics

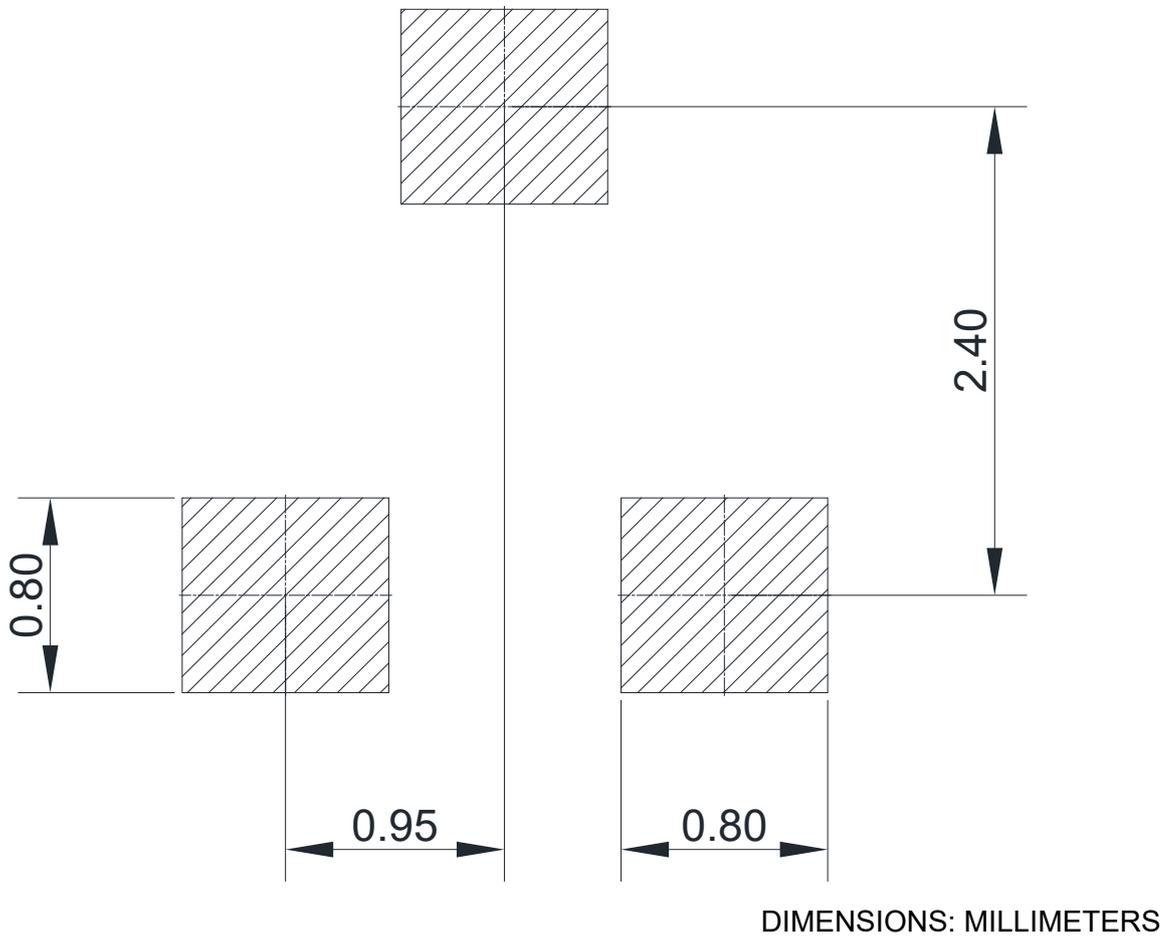
8. Dimension (SOT-23)

POD(Z)



COMMON DIMENSIONS CUNITS MEASURE=MILLIMETER					
SYMBOL	MIN	MAX	SYMBOL	MIN	MAX
A	0.90	1.20	E	2.25	2.55
A1	0.00	0.10	E1	1.20	1.40
A2	0.90	1.10	e	1.80	2.00
b	0.30	0.50	L	0.30	0.50
c	0.07	0.18	L1	0.475	0.625
D	2.80	3.04	θ	0°	8°

9. Recommended Soldering Footprint



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